

# **GN4014ZB4LD, GN4014ZB4LS,** GN4014ZB4LM

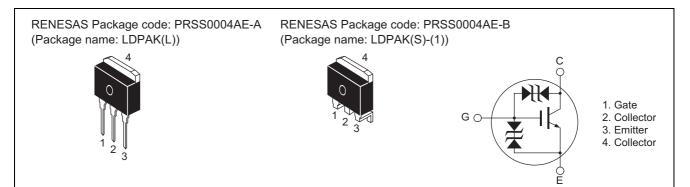
Silicon IGBT Ignition Coil Driver

REJ03G1249-0300 Rev.3.00 Jun 01, 2009

### **Features**

- Including Clamping Zener  $V_{CL} = 400 \ V(typ)$
- Low saturation Voltage  $V_{\text{CE(sat)}} = 1.4 \text{ V(typ)}$
- SMD package LDPAK

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V <sub>CES</sub>	370	V
Gate to Emitter voltage	V <sub>GES</sub>	±20	V
Emitter to Collector voltage	V <sub>ECS</sub>	24	V
Collector current	Ic	14	А
Collector peak current	i <sub>C(peak)</sub>	18	А
Collector power dissipation	P <sub>C</sub> <sup>Note1</sup>	60	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

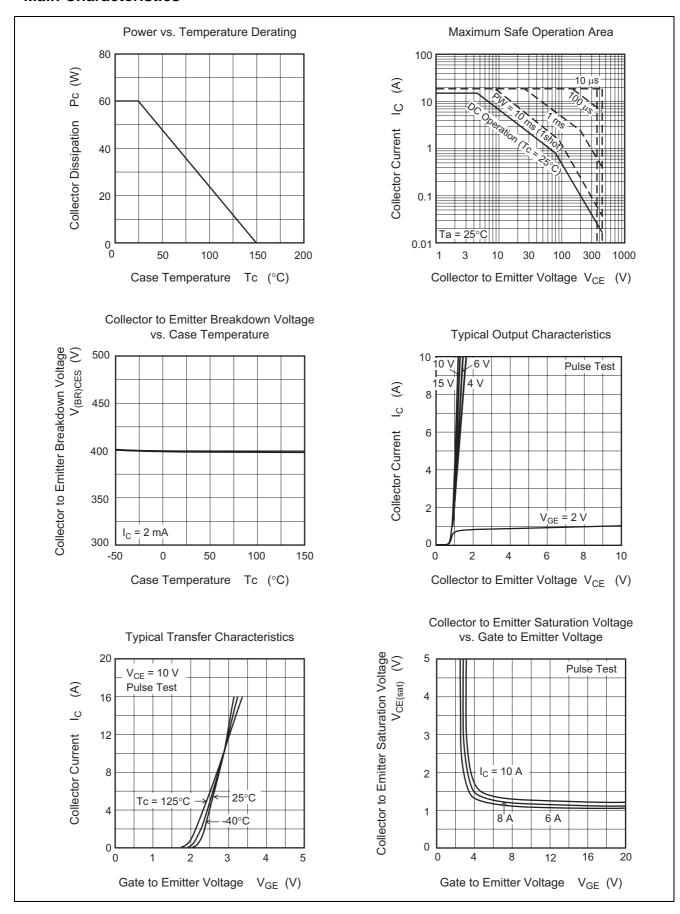
Notes: 1. Value at Tc = 25°C

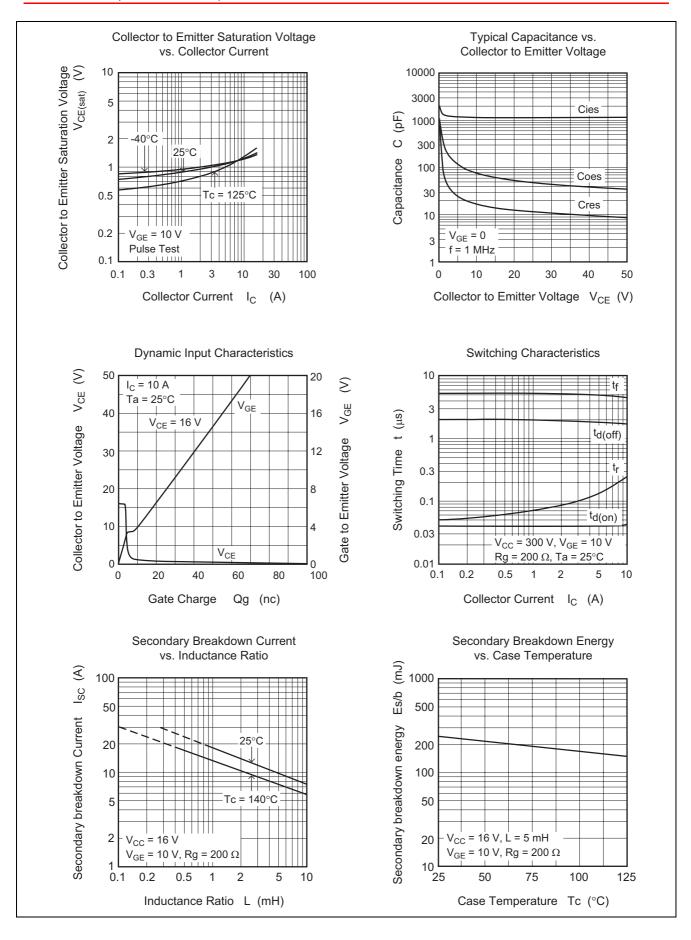
### **Electrical Characteristics**

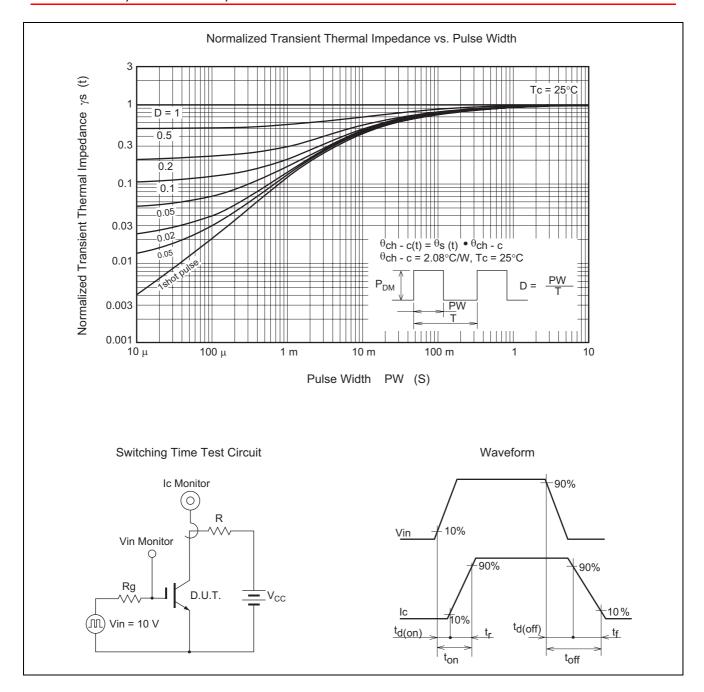
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to Emitter breakdown voltage	$V_{(BR)CES}$	370	400	430	V	$I_c = 2 \text{ mA}, V_{GE} = 0 \text{ V}$
Gate to Emitter breakdown voltage	V <sub>(BR)GES</sub>	±20	_	_	V	$I_G = \pm 100 \mu\text{A},  V_{CE} = 0 \text{V}$
Collector cutoff current	I <sub>CES</sub>	_	_	100	μΑ	$V_{CE} = 300 \text{ V}, V_{GE} = 0 \text{ V}$
Gate cutoff current	I <sub>GES</sub>	_	_	±100	μΑ	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}$
Collector to emitter saturation voltage	V <sub>CE(sat)1</sub>	_	1.4	1.7	V	$I_C = 8 A, V_{GE} = 10 V$
Collector to emitter saturation voltage		_	1.6	2.2	V	I <sub>C</sub> = 8 A, V <sub>GE</sub> = 4 V
Gate to emitter cutoff voltage	$V_{GE(off)}$	1.3		2.2	V	$I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$
Turn-on delay time	t <sub>d(on)</sub>		0.2	_	μs	$V_{CE} = 300 \text{ V}, R_L = 50 \Omega,$
Rise time	t <sub>r</sub>		0.4		μs	$V_{GE}$ = 5 V, $R_G$ = 200 $\Omega$
Turn-off delay time	t <sub>d (off)</sub>	_	1.0		μs	
Fall time	t <sub>f</sub>	_	5		μs	
Input capacitance	Ciss	_	1110	_	pF	$V_{CE} = 10 \text{ V}, V_{GE} = 0,$
Output capacitance	Coss	_	75	_	pF	f = 1 MHz
Reveres transfer capacitance	Cres	_	18	_	pF	
Secondary breakdown energy	Es/b	230	_	_	mJ	L = 5 mH

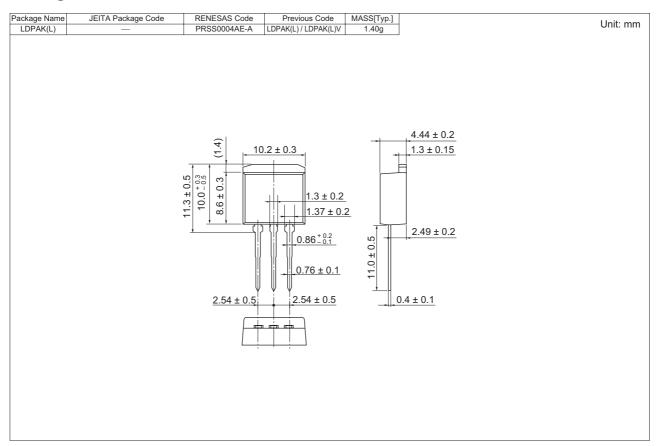
### **Main Characteristics**

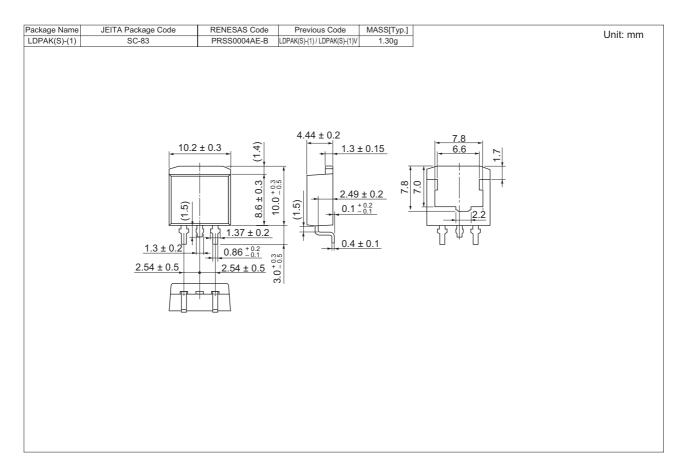






### **Package Dimensions**





### **GN4014ZB4LD, GN4014ZB4LS, GN4014ZB4LM**

## **Ordering Information**

Part Name	Quantity	Shipping Container
GN4014ZB4LD	50 pcs.	Sack
GN4014ZB4LS	1000 pcs.	Taping
GN4014ZB4LM	1000 pcs.	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510